### **SPTECH Silicon NPN Power Transistor**

2SC3157

#### **DESCRIPTION**

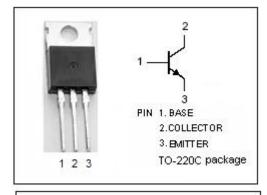
- · Low Collector Saturation Voltage-
- : V<sub>CE(sat)</sub>= 0.6V(Max.)@I<sub>C</sub>= 5A
- Fast Switching Speed
- Complement to Type 2SA1261

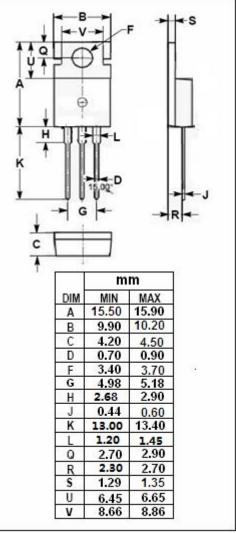
#### **APPLICATIONS**

 Developed for high-voltage high-speed switching, and is ideal for use as a driver in devices such as switching reglators, DC/DC converters, and high frequency power amplifiers.



SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	150	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	100	V	
V <sub>EBO</sub>	Emitter-Base Voltage	7.0	V	
Ic	Collector Current-Continuous	10	А	
I <sub>CM</sub>	Collector Current-Peak	20	А	
lΒ	Base Current-Continuous	3.5	А	
Pc	Collector Power Dissipation @ T <sub>a</sub> =25°C	1.5	W	
	Collector Power Dissipation @ T <sub>C</sub> =25°C	60		
TJ	Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$	





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### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	100		V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5.0A; I <sub>B</sub> = 0.5A		0.6	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5.0A; I <sub>B</sub> = 0.5A		1.5	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 100V; I <sub>E</sub> = 0		10	μА
I <sub>CEX</sub>	Collector Cutoff Current	V <sub>CE</sub> = 100V; V <sub>BE(off)</sub> = -1.5V V <sub>CE</sub> = 100V; V <sub>BE(off)</sub> = -1.5V, T <sub>a</sub> =125°C		10 1.0	μA mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		10	μ <b>А</b>
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V	40	200	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3.0A; V <sub>CE</sub> = 5V	40	200	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 5.0A; V <sub>CE</sub> = 5V	20		
Switching times					
t <sub>on</sub>	Turn-on Time			0.5	μs

t <sub>on</sub>	Turn-on Time	$I_{C}$ = 5.0A, $R_{L}$ = 10 $\Omega$ , $I_{B1}$ = - $I_{B2}$ = 0.5A, $V_{CC}$ $\approx$ 50V	0.5	μs
t <sub>stg</sub>	Storage Time		1.5	μς
t <sub>f</sub>	Fall Time		0.5	μς

## ♦ h<sub>FE-2</sub> Classifications

M	L	К
40-80	60-120	100-200

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